



# BUK7Y9R9-80E

N-channel 80 V, 9.9 mΩ standard level MOSFET in LPAK56

8 May 2013

Product data sheet

## 1. General description

Standard level N-channel MOSFET in an LPAK56 (Power SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

## 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with  $V_{GS(th)}$  rating of greater than 1 V at 175 °C

## 3. Applications

- 12 V, 24 V and 48 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	80	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 1</a>	-	-	89	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	-	195	W
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $T_j = 25\text{ °C}$ ; <a href="#">Fig. 11</a>	-	7.3	9.9	mΩ
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 25\text{ A}$ ; $V_{DS} = 64\text{ V}$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>	-	14.4	-	nC

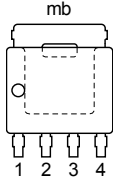
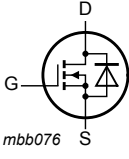


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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p><b>LPAK56; Power-SO8 (SOT669)</b></p>	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7Y9R9-80E	LPAK56; Power-SO8	Plastic single-ended surface-mounted package (LPAK56; Power-SO8); 4 leads	SOT669

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7Y9R9-80E	79E980

## 8. Limiting values

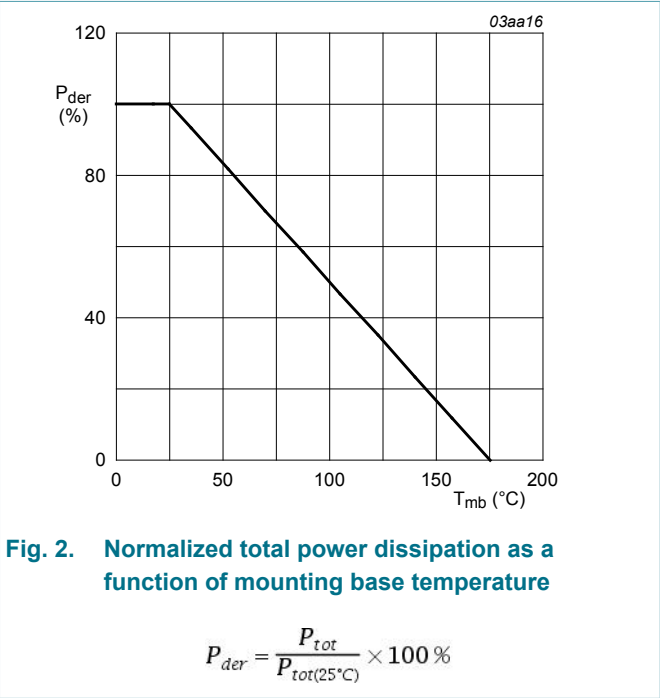
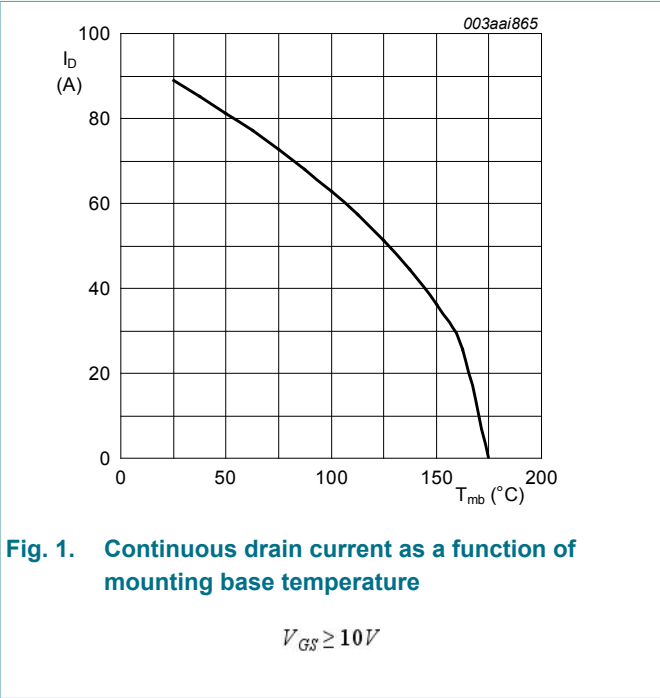
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	80	V
$V_{DGR}$	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	80	V
$V_{GS}$	gate-source voltage	$T_j \leq 175\text{ °C}$ ; DC	-20	20	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 1</a>	-	89	A
		$T_{mb} = 100\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; <a href="#">Fig. 1</a>	-	63	A
$I_{DM}$	peak drain current	$T_{mb} = 25\text{ °C}$ ; pulsed; $t_p \leq 10\text{ }\mu\text{s}$ ; <a href="#">Fig. 4</a>	-	354	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; <a href="#">Fig. 2</a>	-	195	W
$T_{stg}$	storage temperature		-55	175	°C

Symbol	Parameter	Conditions		Min	Max	Unit
T <sub>j</sub>	junction temperature			-55	175	°C
Source-drain diode						
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	89	A
I <sub>SM</sub>	peak source current	pulsed; t <sub>p</sub> ≤ 10 μs; T <sub>mb</sub> = 25 °C		-	354	A
Avalanche ruggedness						
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	I <sub>D</sub> = 89 A; V <sub>sup</sub> ≤ 80 V; R <sub>GS</sub> = 50 Ω; V <sub>GS</sub> = 10 V; T <sub>j(init)</sub> = 25 °C; unclamped; Fig. 3	[1][2]	-	106	mJ

[1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.  
[2] Refer to application note AN10273 for further information.



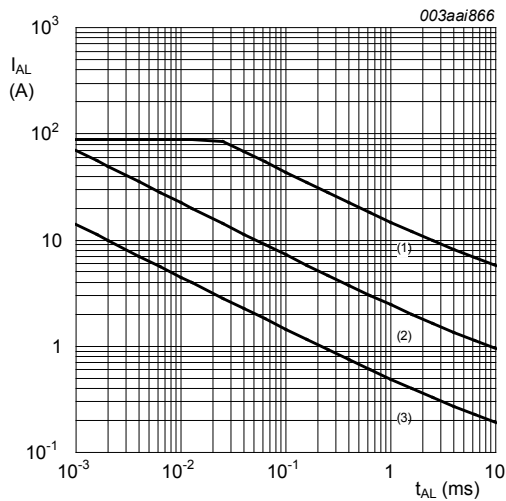


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1)  $T_{j\ (init)} = 25^{\circ}C$ ; (2)  $T_{j\ (init)} = 150^{\circ}C$ ; (3) Repetitive Avalanche

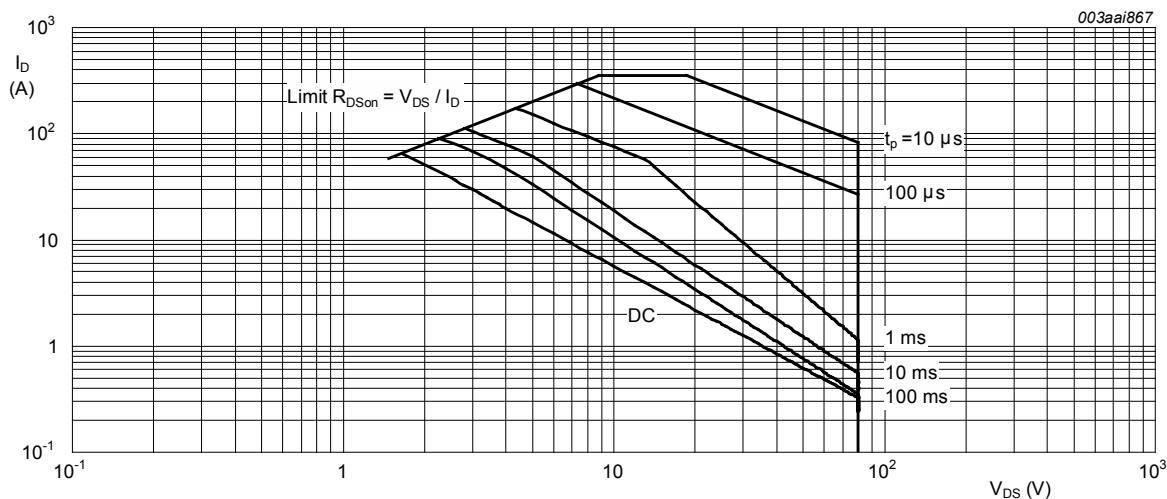


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$ ;  $I_{DM}$  is a single pulse

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	0.77	K/W

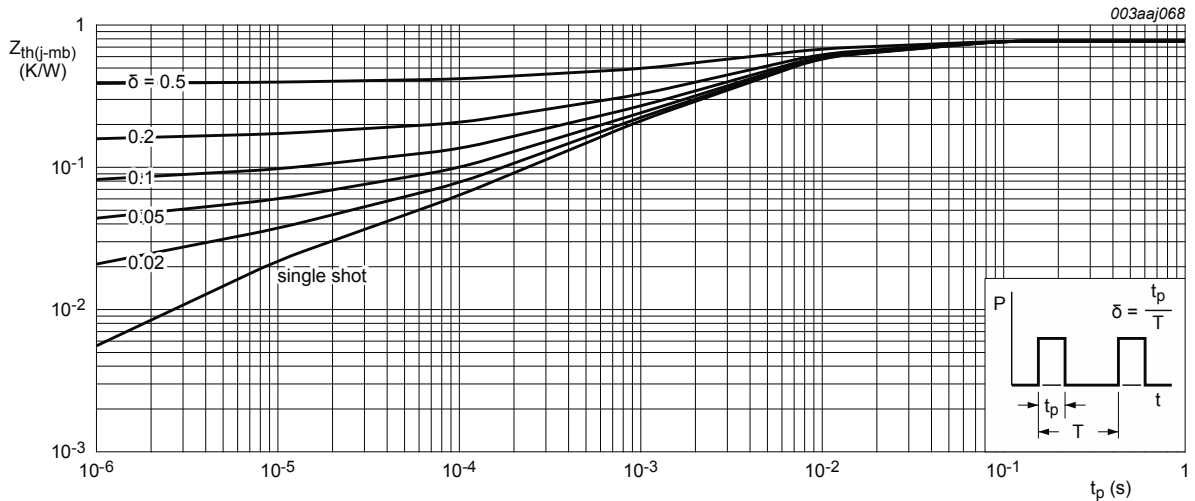


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\ \mu A$ ; $V_{GS} = 0\ V$ ; $T_j = 25\ ^\circ C$		80	-	-	V
		$I_D = 250\ \mu A$ ; $V_{GS} = 0\ V$ ; $T_j = -55\ ^\circ C$		72	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1\ mA$ ; $V_{DS} = V_{GS}$ ; $T_j = 25\ ^\circ C$ ; <a href="#">Fig. 9</a> ; <a href="#">Fig. 10</a>		2.4	3	4	V
		$I_D = 1\ mA$ ; $V_{DS} = V_{GS}$ ; $T_j = -55\ ^\circ C$ ; <a href="#">Fig. 9</a>		-	-	4.5	V
		$I_D = 1\ mA$ ; $V_{DS} = V_{GS}$ ; $T_j = 175\ ^\circ C$ ; <a href="#">Fig. 9</a>		1	-	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 80\ V$ ; $V_{GS} = 0\ V$ ; $T_j = 25\ ^\circ C$		-	0.13	10	$\mu A$
		$V_{DS} = 80\ V$ ; $V_{GS} = 0\ V$ ; $T_j = 175\ ^\circ C$		-	-	500	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 20\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$		-	2	100	nA
		$V_{GS} = -20\ V$ ; $V_{DS} = 0\ V$ ; $T_j = 25\ ^\circ C$		-	2	100	nA
$R_{DSon}$	drain-source on-state resistance	$V_{GS} = 10\ V$ ; $I_D = 25\ A$ ; $T_j = 175\ ^\circ C$ ; <a href="#">Fig. 11</a> ; <a href="#">Fig. 12</a>		-	-	24.9	m $\Omega$
		$V_{GS} = 10\ V$ ; $I_D = 25\ A$ ; $T_j = 25\ ^\circ C$ ; <a href="#">Fig. 11</a>		-	7.3	9.9	m $\Omega$
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	$I_D = 25\ A$ ; $V_{DS} = 64\ V$ ; $V_{GS} = 10\ V$ ; <a href="#">Fig. 13</a> ; <a href="#">Fig. 14</a>		-	51.6	-	nC
$Q_{GS}$	gate-source charge			-	14.1	-	nC
$Q_{GD}$	gate-drain charge			-	14.4	-	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz; T <sub>j</sub> = 25 °C; <a href="#">Fig. 15</a>		-	3200	4266	pF
C <sub>oss</sub>	output capacitance			-	303	364	pF
C <sub>rss</sub>	reverse transfer capacitance			-	165	226	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 60 V; R <sub>L</sub> = 2.4 Ω; V <sub>GS</sub> = 10 V; R <sub>G(ext)</sub> = 5 Ω		-	15	-	ns
t <sub>r</sub>	rise time			-	23	-	ns
t <sub>d(off)</sub>	turn-off delay time			-	34	-	ns
t <sub>f</sub>	fall time			-	21	-	ns
Source-drain diode							
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 16</a>		-	0.83	1.2	V
t <sub>rr</sub>	reverse recovery time	I <sub>S</sub> = 20 A; dI <sub>S</sub> /dt = -100 A/μs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V		-	35	-	ns
Q <sub>r</sub>	recovered charge			-	52	-	nC

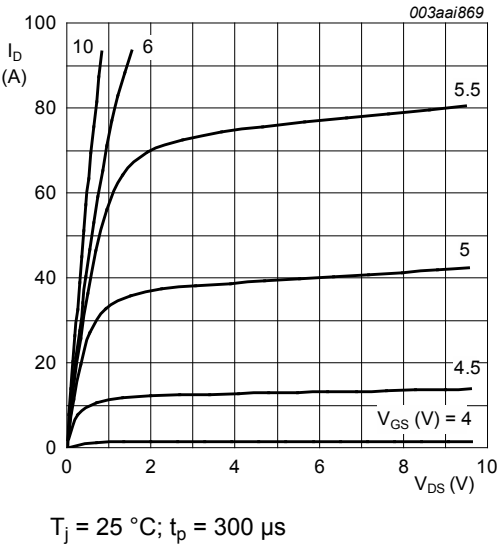


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

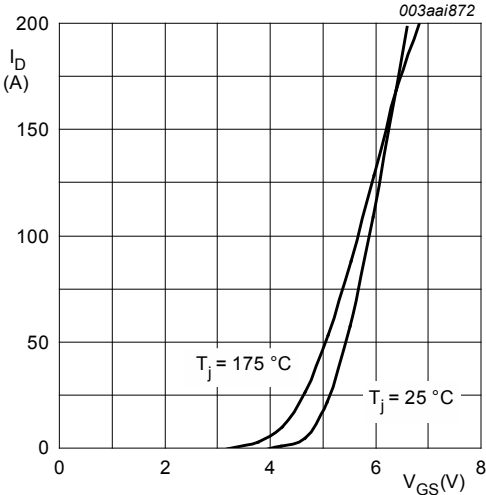


Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values

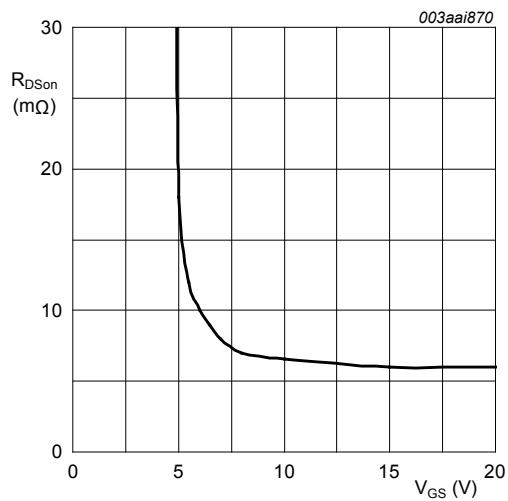


Fig. 8. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25^{\circ}\text{C}; I_D = 25\text{A}$

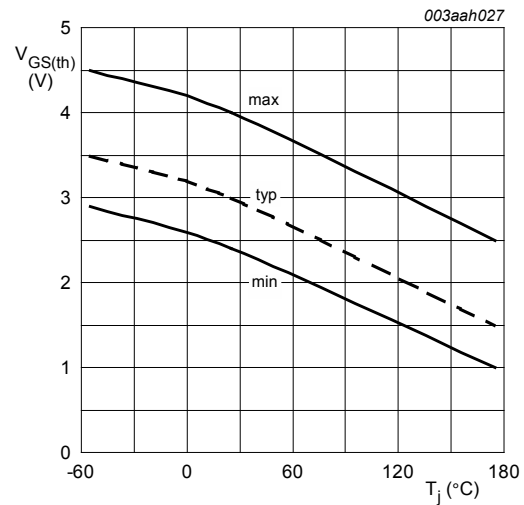


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{mA}; V_{DS} = V_{GS}$

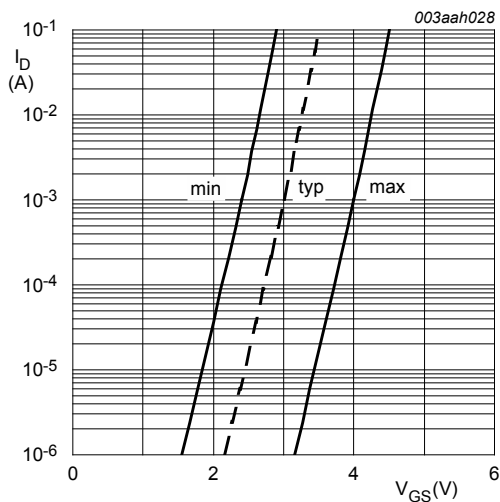


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25^{\circ}\text{C}; V_{DS} = 5\text{V}$

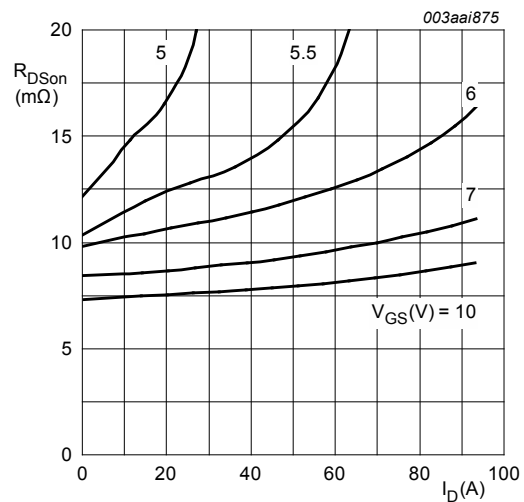


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$T_j = 25^{\circ}\text{C}; t_p = 300\text{ }\mu\text{s}$

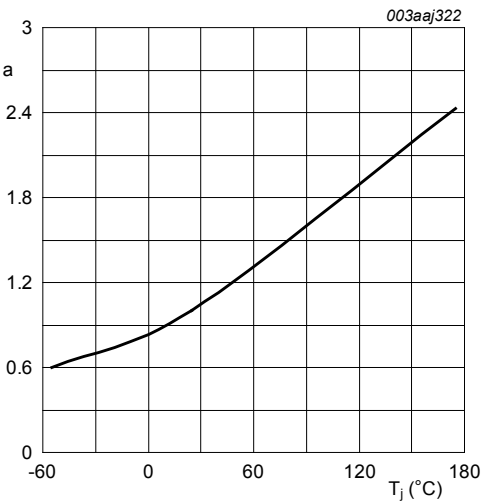


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DS(on)}}{R_{DS(on)}(25^\circ\text{C})}$$

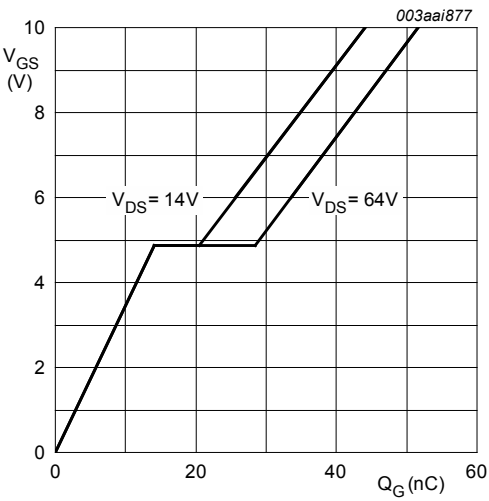


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^\circ\text{C}; I_D = 25\text{A}$$

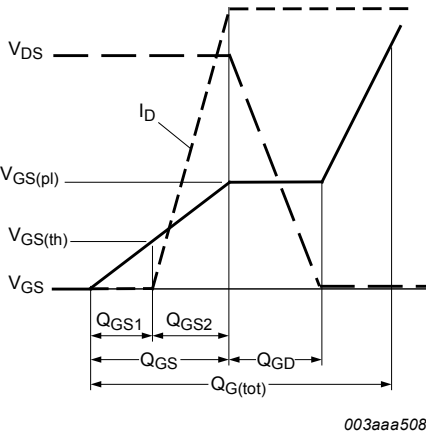


Fig. 14. Gate charge waveform definitions

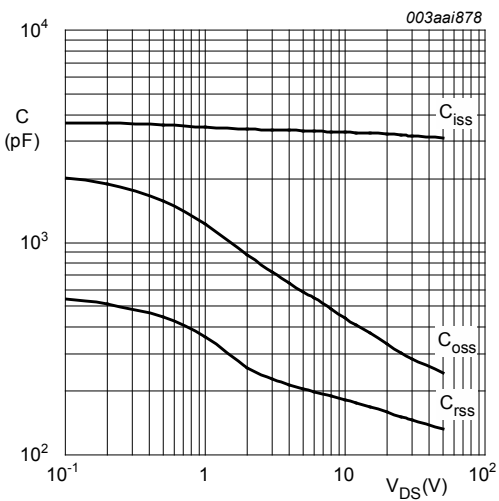


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{V}; f = 1\text{MHz}$$



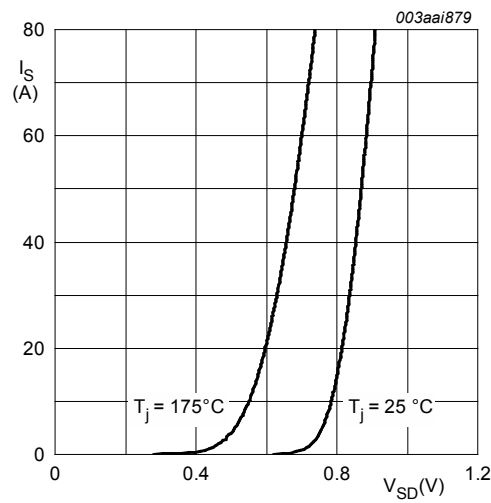


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

11. Package outline

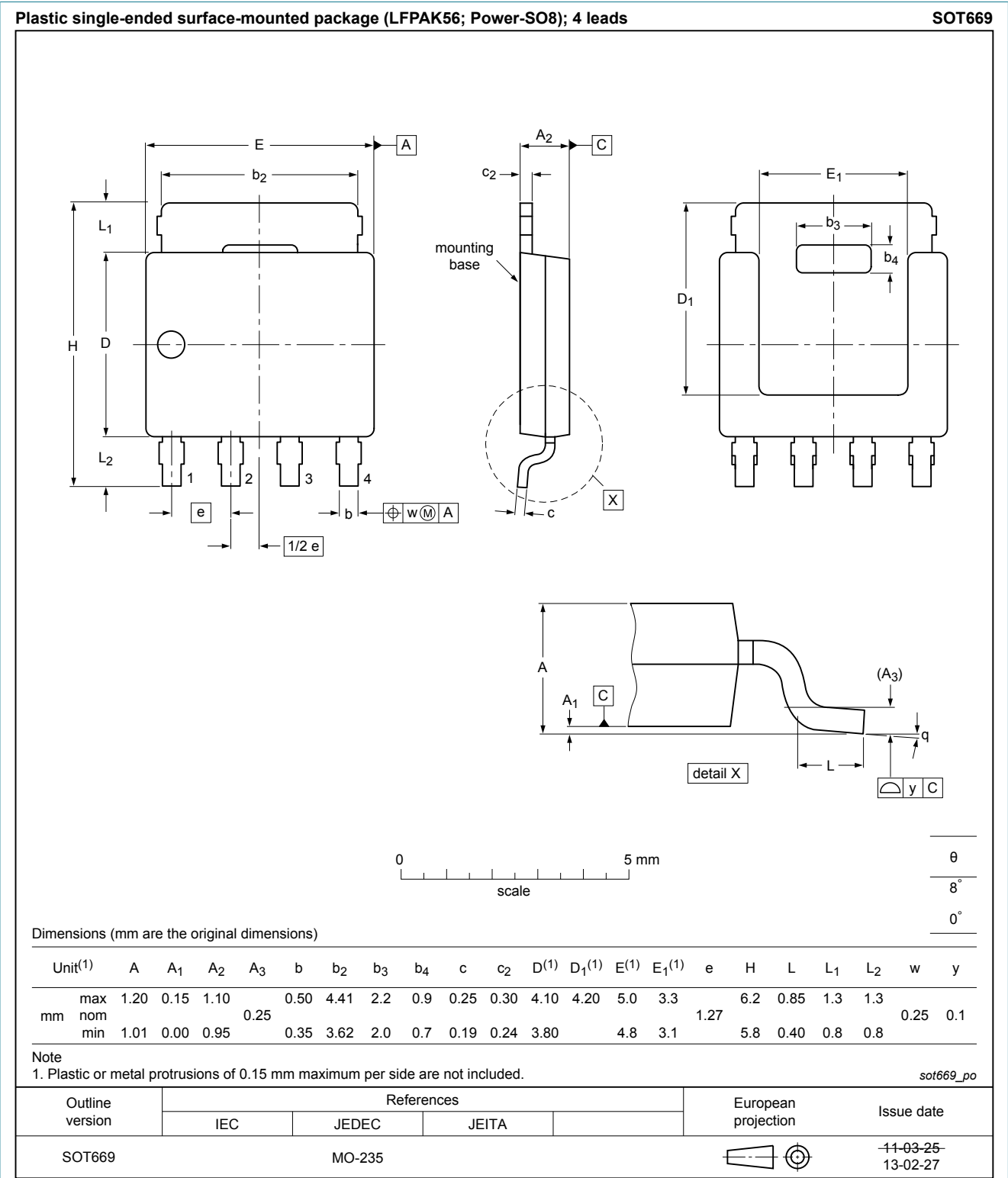


Fig. 17. Package outline LPAK56; Power-SO8 (SOT669)

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13. Contents

1	General description .....	1
2	Features and benefits .....	1
3	Applications .....	1
4	Quick reference data .....	1
5	Pinning information .....	2
6	Ordering information .....	2
7	Marking .....	2
8	Limiting values .....	2
9	Thermal characteristics .....	4
10	Characteristics .....	5
11	Package outline .....	10
12	Legal information .....	11
12.1	Data sheet status .....	11
12.2	Definitions .....	11
12.3	Disclaimers .....	11
12.4	Trademarks .....	12

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